REMARKS

Claims 9-41 and 47-59 are pending in the application with claims 1-8 and 42-46 canceled herein as being drawn toward the non-elected species. Applicant hereby elects the species of Group II, claims 9-41 and 47-59 without traverse. Applicant requests consideration of the elected claims.

Applicant herein amends the specification to correct a typographical error. It is apparent from the discussion surrounding line 16 of page 20 that the term "500 Torr" contains a typographical error and should instead indicate "500 milliTorr." Page 19, line 3 to page 20, line 23 discuss various CVD processes. The portion of such text amended herein pertains to a low temperature, low pressure deposition and it is thus apparent from the context that the text as amended herein was intended at the time of filing. Accordingly, the amendment herein does not set forth new matter.

Applicant respectfully request entry of the amendment herein and consideration of the currently pending claims.

Respectfully submitted,

Dated: 26 Sep 2002 By: _____

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Filing Date ..... August 21, 2000
Inventor ..... Gary A. Mercaldi
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Group Art Unit 2823
Examiner ..... T. Dang
Attorney's Docket No. MI22-1358
Title: Low Selectivity Deposition Methods

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING RESPONSE TO August 27, 2002 OFFICE ACTION

In the Specification

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

The paragraph beginning at line 8 on page 20 has been amended as follows:

Further, forming a deposition layer may occur by unconventional CVD in a process regime so far outside conventional CVD that the deposition is substantially selective. That is, multiple deposition species may contact the substrate together in the deposition chamber. However, temperature and pressure are low enough that the thickness of the deposition layer over a first part of a substrate is less than 50% of a thickness of the deposition layer over a second part, as shown in Fig. 2. Exemplary parameters include less than about 645 °C and less than about 500 ~~Torr~~ milliTorr or perhaps different ranges, as determinable by those skilled in the art, depending on above mentioned factors. In such a process regime, pressure might bear a more significant effect on selectivity compared to temperature. The unconventional CVD process regime may be conducive to forming a deposition layer only about 1 to 5 atoms or molecules thick. Accordingly, by using a nucleation layer in keeping with the various aspects of the present invention, unconventional CVD may also be used to form a deposition layer.